

IN THE SPECIFICATION:

Kindly amend the specification as follows.

1. Please replace the third full paragraph on page 3 beginning with “For example,” with the following new paragraph.

For example, with the TOKU-KAI No.2001-141540, the TOKU-KAI No.2001-141541, there is provided a heat resistance layer E₆ on the outermost layer of a film E formed on the upper face of the frame D made from a silicon substrate A as shown in Figure 18. With Figure [16] 18, E₁~E₃ designate silicon oxide layers to form a film E, E₄ a silicon nitride layer, E₅ platinum, and C a lead connecting hardware.

2. Please replace the paragraph beginning on page 3 under the heading “Object of the Invention,” with the following new paragraph.

With the silicon-made ultra-small-sized mass flow rate sensor illustrated in the aforementioned Figure 18, a silicon nitride [S₄] E₄ layer formed on the lower face side of a frame D and a heat resistance layer E₆ comprising a silicon nitride layer to form a film E have been provided to enhance water resistance and moisture resistance. However, it is far from the fundamental solution for the problems such as the afore-mentioned corrosion and the like due to the reason that the frame D itself is formed with a silicon substrate A.